DISCRETE SEMICONDUCTORS

DATA SHEET

PEMH7; PUMH7 NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

Product data sheet Supersedes data of 2001 Oct 22 2003 Oct 02



NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PEMH7; PUMH7

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
I _O	output current (DC)	_	100	mA
TR1	NPN	_	_	
TR2	NPN	_	_	
R1	bias resistor	4.7	_	kΩ
R2	bias resistor	open	_	

QUICK REFERENCE DATA

DESCRIPTION

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER PACKAGE		MARKING CODE ⁽¹⁾	NPN/PNP	PNP/PNP	
TIPE NOMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	
PEMH7	SOT666	_	H3	PEMD6	PEMB3
PUMH7	SOT363	SC-88	H*7	PUMD6	PUMB3

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TIPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION		
PEMH7		1	emitter TR1		
PUMH7	6 5 4	2	base TR1		
		3	collector TR2		
	TR2	4	emitter TR2		
	TR1	5	base TR2		
		6	collector TR1		
	1 2 3				
	Top view MAM453				

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ORDERING INFORMATION

TYPE NUMBER		PACKAGE						
ITPE NUMBER	NAME	DESCRIPTION	VERSION					
PEMH7	_	Plastic surface mounted package; 6 leads	SOT666					
PUMH7	1	Plastic surface mounted package; 6 leads	SOT363					

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	tor		•	•	- 1
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	•				•
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	300	mW
ı	SOT666	notes 1 and 2	_	300	mW

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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PEMH7; PUMH7

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT	
Per transis	stor		•	•	•	
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA
I _{CEO}	collector-emitter cut-off current $V_{CE} = 30 \text{ V}; I_B = 0$		_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	330	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	_	_	100	mV
R1	input resistor		3.3	4.7	6.1	kΩ
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	_	2.5	pF

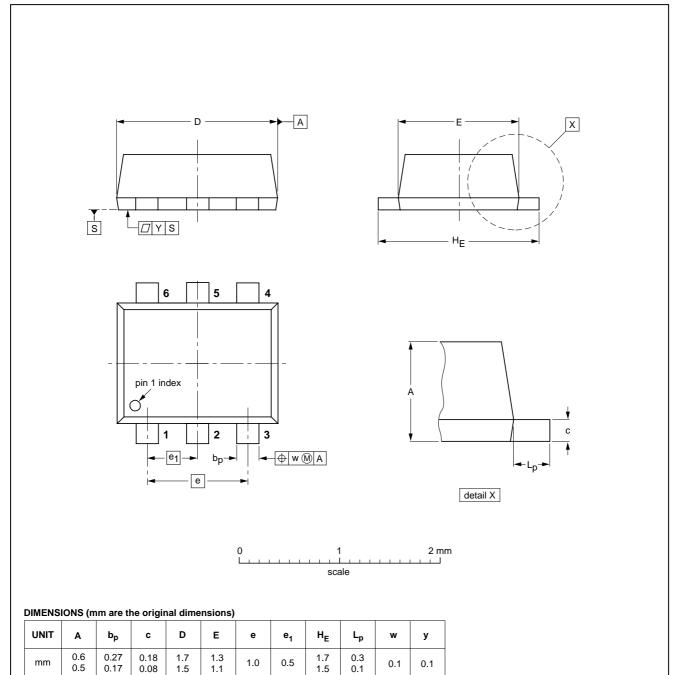
NPN/NPN resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, R2 = open

PEMH7; PUMH7

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

0.1

1.0

0.5

2003 Oct 02 5

0.08

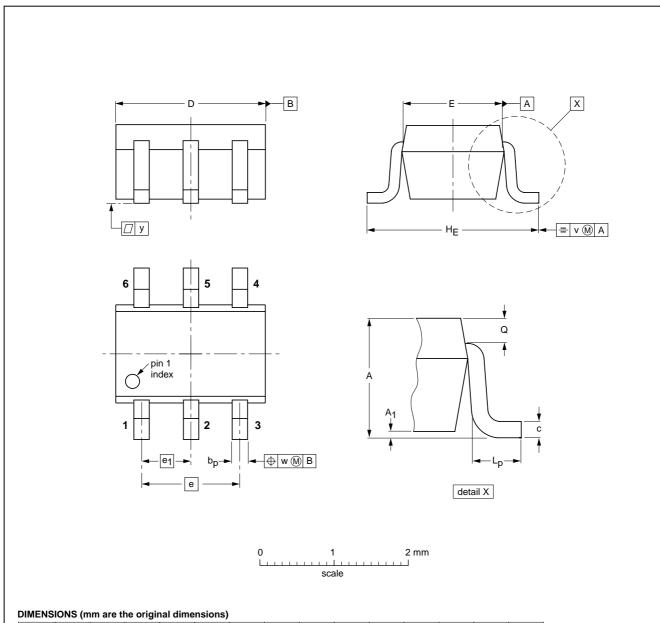
mm

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

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Plastic surface mounted package; 6 leads

SOT363



UNIT	А	A ₁ max	bp	С	D	Е	е	e ₁	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	IEC JEDEC EIAJ F		PROJECTION	ISSUE DATE	
SOT363			SC-88			97-02-28

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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